

MATERIAL FOR FORMING HAFNIUM-BASED OXIDE FILM

Patent Number: JP2002093804
Publication date: 2002-03-29
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Requested Patent: JP2002093804
Application Number: JP20000282198 20000918
Priority Number(s):
IPC Classification: H01L21/316; C23C16/40; H01L29/78
EC Classification:
Equivalents:

Abstract

PROBLEM TO BE SOLVED: To efficiently provide a technique for forming a neat hafnium-based film.
SOLUTION: A compound which is expressed by a chemical formula $(R_1R_2N)_4Hf$ is used.

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